

/ Descriptions

TO-220 N MOS N-CHANNEL MOSFET in a TO-220 Plastic Package.

/ Features

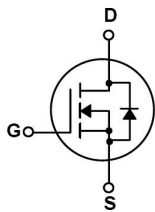
Low gate charge, low crss, fast switching.

/ Applications

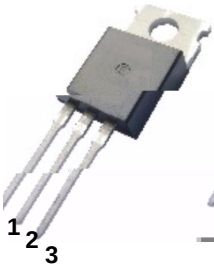
DC/DC

These devices are well suited for high efficiency switching DC/DC converters and switch mode power supplies.

/ Equivalent Circuit



/ Pinning



PIN1 G PIN 2 D PIN 3 S

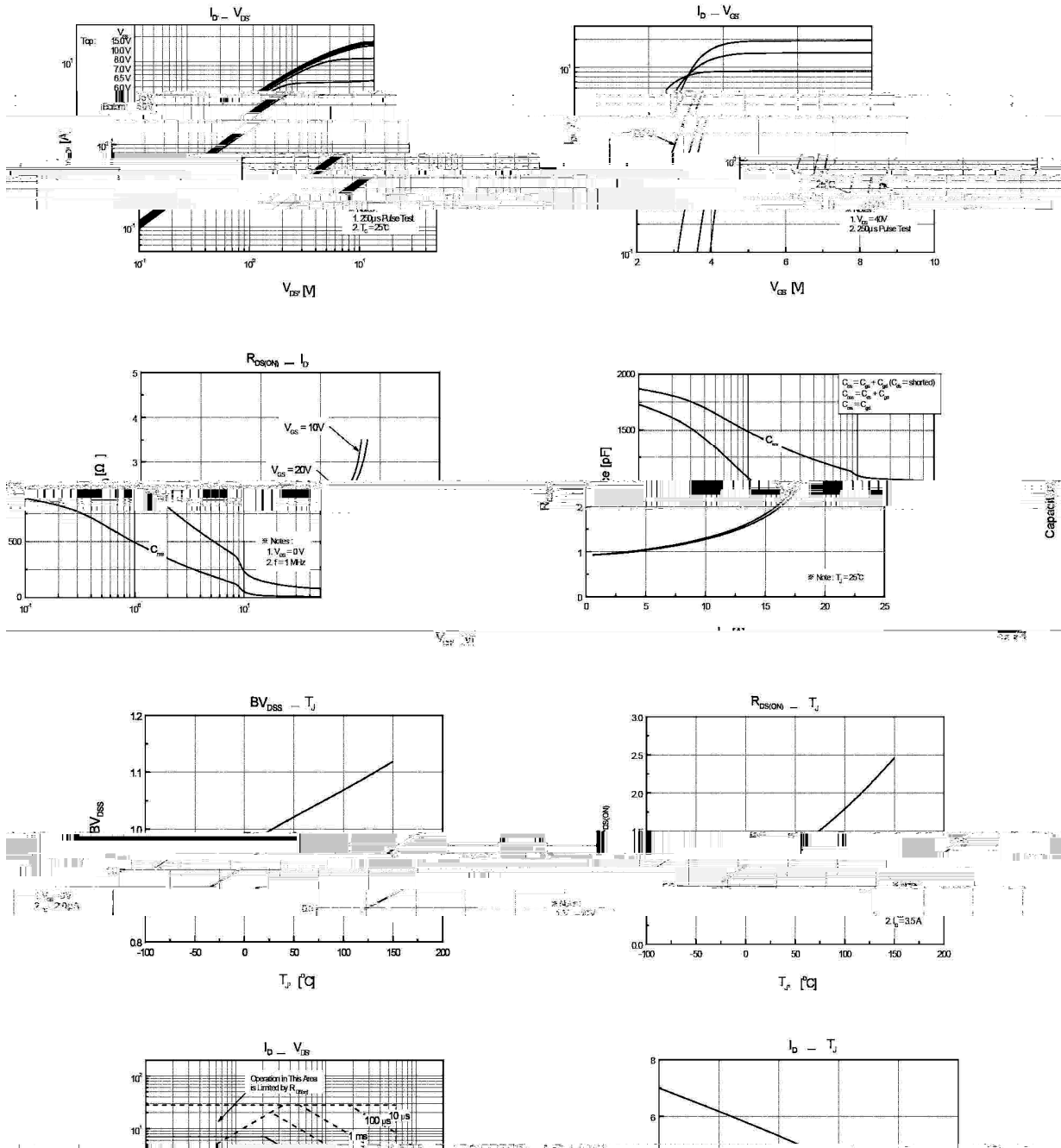
/ h_{FE} Classifications & Marking

See Marking Instructions.

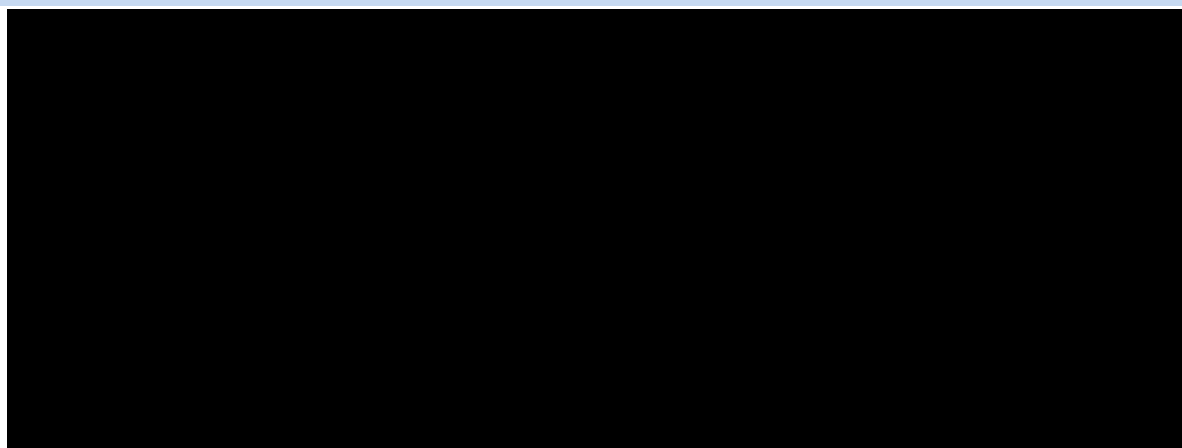
	Symbol	Rating	Unit
	V_{DSS}	650	V
	$I_D(T_C=25^\circ\text{C})$	7.0	A
	$I_D(T_C=100^\circ\text{C})$	4.4	A
	I_{DM}	28	A
	V_{GS}	± 30	V
	E_{AS}	420	mJ
	E_{AR}	14.7	mJ
	I_{AR}	7.0	A
	$P_D(T_C=25^\circ\text{C})$	147	W
Range	T_J, T_{STG}	-55 to 150	$^\circ\text{C}$

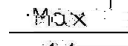
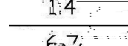
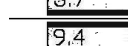
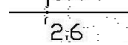
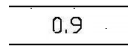
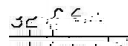
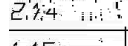
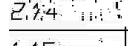
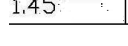
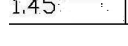
Symbol	Test Conditions	Min	Typ	Max	Unit
V_{DSS}	$V_{GS}=0V$ $I_D=250\mu A$	650			V
I_{DSS}	$V_{DS}=650V$ $V_{GS}=0V$			1.0	μA
	$V_{DS}=520V$ $T_C=125^\circ\text{C}$			100	μA
I_{GSS}	$V_{GS}=\pm 30V$ $V_{DS}=0V$			± 100	nA
$V_{GS(th)}$	$V_{DS}=V_{GS}$ $I_D=250\mu A$	2.0		4.0	V
$r_{DS(on)}$	$V_{GS}=10V$ $I_D=3.5A$			1.3	Ω
g_{FS}	$V_{DS}=40V$ $I_D=3.5A$		8.2		S
V_{SD}	$V_{GS}=0V$ $I_S=7.0A$			1.4	V
C_{iss}	$V_{DS}=25V$ $V_{GS}=0V$ $f=1.0\text{MHz}$		1100	1500	pF
C_{oss}			110	150	pF

/ Electrical Characteristic Curve

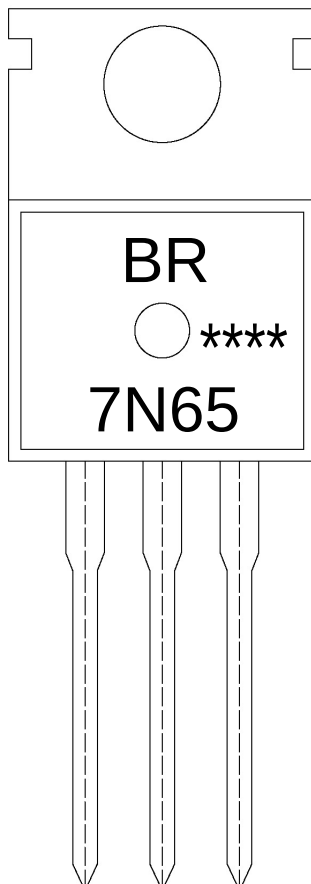


/ Package Dimensions



Dimensions in Millimeters			Dimensions in Millimeters		
Max	Symbol	Min	Max	Symbol	Min
14		9.8	10.2	C	1.2
6.7		3.56	3.64	B	6.34
9.4		15.7	16.1	B1	9.0
2.6		2.26	3.6	C1	2.2
0.9		9.6	10.6	a1	0.7
32.6		0.4	0.6		0.4
2.74		1.25	1.7		0.234
1.45				0.2	1.25

/ Marking Instructions



BR

7N65

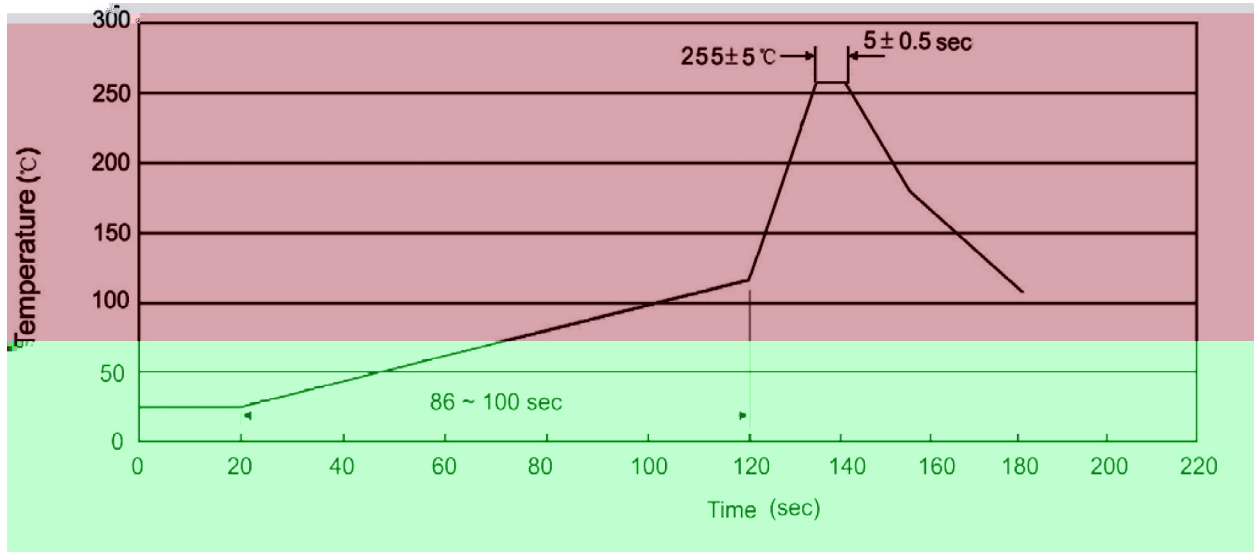
Note:

BR: Company Code

7N65: Product Type.

****: Lot No. Code, code change with Lot No.

() / Temperature Profile for Dip Soldering(Pb-Free)



Note:

1 25 150